

N-Channel 40-V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{(BR)DSS} (V)	$V_{(BR)DSS}(V)$ $r_{DS(on)}(\Omega)$			
40	0.0074 at V _{GS} = 10 V	70 ^a		
40	0.011 at V _{GS} = 4.5 V	67		

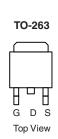
FEATURES

- TrenchFET® Power MOSFET
- 175 °C Junction Temperature
- Low Threshold

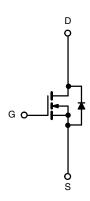


APPLICATIONS

Motor Control



Ordering Information: SUM70N04-07L-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T _C = 25 °C, unless oth	erwise noted		
Parameter	-	Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	40	V
Gate-Source Voltage		V _{GS}	± 20	V
Continuous Drain Current (T _{.I} = 175 °C)	T _C = 25 °C	1-	70 ^a	
Continuous Diain Current (1) = 175 C)	T _C = 125 °C	l _D	47	A
Pulsed Drain Current		I _{DM}	120	7
Avalanche Current		I _{AR}	40	
Repetitive Avalanche Energy ^b	L = 0.1 mH	E _{AR}	80	mJ
Mariana Barra Biratan b	T _C = 25 °C	В	100 ^c	w
Maximum Power Dissipation ^b	T _A = 25 °C ^d	$ P_D$ $-$	3.75	vv
Operating Junction and Storage Temperature Range		T _J , T _{stq}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Limit	Unit		
Junction-to-Ambient	PCB Mount ^d	R _{thJA}	40	°C/W		
Junction-to-Case		R _{thJC}	1.4	J 5/VV		

Notes:

- a. Package limited.
- b. Duty cycle \leq 1 %.
- c. See SOA curve for voltage derating.
- d. When Mounted on 1" square PCB (FR-4 material).

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply.

SUM70N04-07L

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Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static	,			, ,.			
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{DS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	40				
Gate-Threshold Voltage	V _{GS(th)}				3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			100	nA	
		V _{DS} = 32 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 32 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 \text{ °C}$			50	μΑ	
		$V_{DS} = 32 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 \text{ °C}$			250		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	100			Α	
		$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$		0.006	0.0074		
Durin Course On Otale Desisters	_	$V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}$		0.0085	0.011		
Drain-Source On-State Resistance ^a	r _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}, T_J = 125 ^{\circ}\text{C}$			0.012	Ω	
		$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}, T_J = 175 ^{\circ}\text{C}$			0.015		
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 30 \text{ A}$	20			S	
Dynamic ^b	•			•	!		
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		2800		pF	
Output Capacitance	C _{oss}			320			
Reverse Transfer Capacitance	C _{rss}			190			
Total Gate Charge ^c	Qg			50	75	nC	
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 50 \text{ A}$		10			
Gate-Drain Charge ^c	Q_{gd}			10			
Gate Resistance	R_{G}			2.0		Ω	
Turn-On Delay Time ^c	t _{d(on)}			11	20		
Rise Time ^c	t _r	V_{DD} = 20 V, R_L = 0.4 Ω		20	30	ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D\cong 50$ A, $V_{GEN}=10$ V, $R_G=2.5~\Omega$		40	60		
Fall Time ^c	t _f			15	25		
Source-Drain Diode Ratings and Cha	aracteristics T	_C = 25 °C ^b					
Continuous Current	I _S				66	Α	
Pulsed Current	I _{SM}				100		
Forward Voltage ^a	V_{SD}	$I_F = 50 \text{ A}, V_{GS} = 0 \text{ V}$		1.0	1.5	V	
Reverse Recovery Time	t _{rr}			30	50	ns	
Peak Reverse Recovery Current	I _{RM(REC)}	$I_F = 50 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$		1.6	2.4	Α	
Reverse Recovery Charge	Q _{rr}			0.024	0.06	μC	

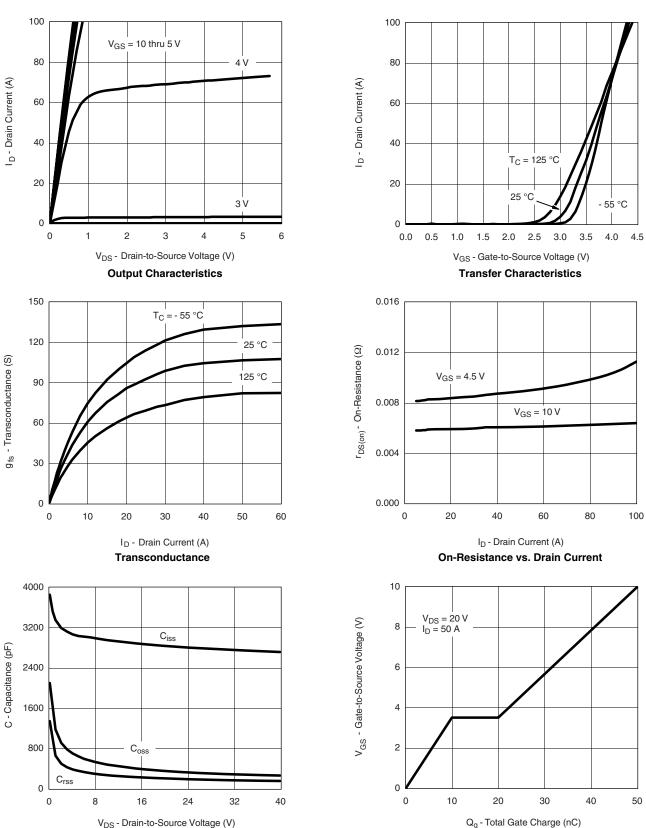
Notes:

- a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



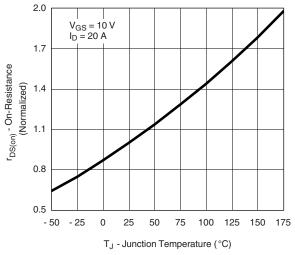
Capacitance

Gate Charge

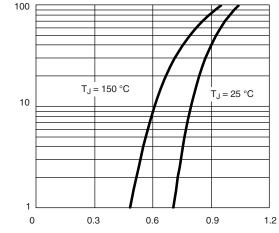
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

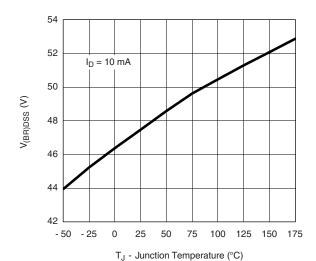






On-Resistance vs. Junction Temperature

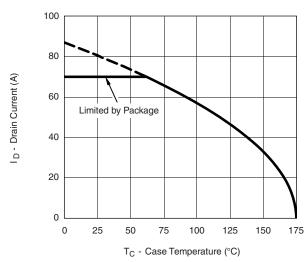
 $\label{eq:VSD-Source-to-Drain Voltage} V_{SD} \mbox{-} \mbox{Source-to-Drain Diode Forward Voltage}$ Source-Drain Diode Forward Voltage



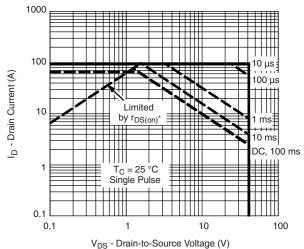
Drain Source Breakdown vs. Junction Temperature



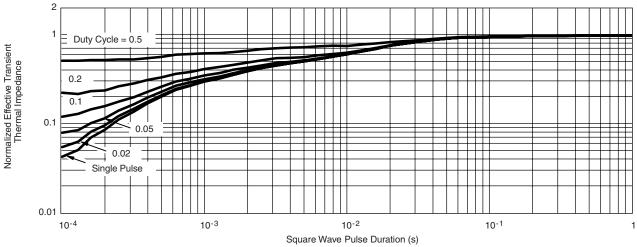
THERMAL RATINGS



Maximum Avalanche and Drain Current vs. Case Temperature



* V_{GS} > minimum V_{GS} at which $r_{DS(on)}$ is specified Safe Operating Area, Junction-to-Case



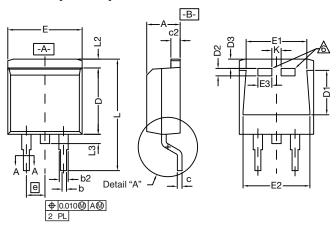
Normalized Thermal Transient Impedance, Junction-to-Case

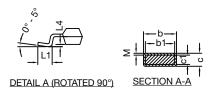
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TO-263 (D²PAK): 3-LEAD





		INC	HES	MILLIN	/IETERS
DIM.		MIN.	MAX.	MIN.	MAX.
Α		0.160	0.190	4.064	4.826
b		0.020	0.039	0.508	0.990
	b1	0.020	0.035	0.508	0.889
	b2	0.045	0.055	1.143	1.397
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
	Thin lead	0.013	0.017	0.330	0.431
c1	Thick lead	0.023	0.027	0.584	0.685
c2		0.045	0.055	1.143	1.397
D		0.340	0.380	8.636	9.652
D1		0.220	0.240	5.588	6.096
D2		0.038	0.042	0.965	1.067
D3		0.045	0.055	1.143	1.397
E		0.380	0.410	9.652	10.414
E1		0.245	-	6.223	-
E2		0.355	0.375	9.017	9.525
E3		0.072	0.078	1.829	1.981
	e 0.100 BSC		2.54	2.54 BSC	
K		0.045	0.055	1.143	1.397
L		0.575	0.625	14.605	15.875
L1		0.090	0.110	2.286	2.794
L2		0.040	0.055	1.016	1.397
L3		0.050	0.070	1.270	1.778
L4		0.010 BSC		0.254 BSC	
М		-	0.002	-	0.050
	N: T10-0738-R G: 5843	ev. J, 03-Ja	n-11		

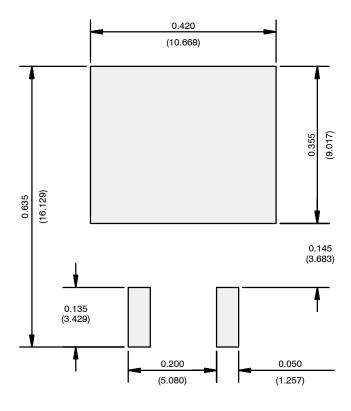
Notes

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



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